



SPP3407D

P-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPP3407D is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

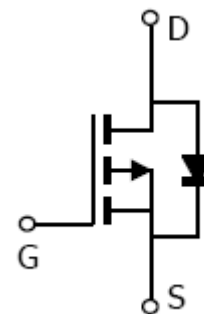
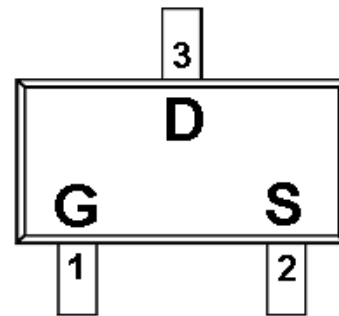
FEATURES

- ◆ -30V/-4.0A, $R_{DS(ON)}=70m\Omega@V_{GS}=-10V$
- ◆ -30V/-3.2A, $R_{DS(ON)}=95m\Omega@V_{GS}=-4.5V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-23 package design

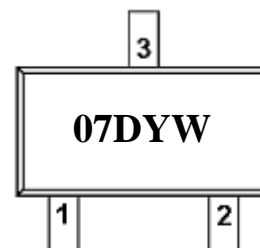
APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

PIN CONFIGURATION(SOT-23)



PART MARKING



Y : Year Code
W : Week Code



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PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPP3407DS23RG	SOT-23	07DYW
SPP3407DS23RGB	SOT-23	07DYW

※ Week Code : A ~ Z (1 ~ 26) ; a ~ z (27 ~ 52)

※ SPP3407DS23RG : Tape Reel ; Pb – Free

※ SPP3407DS23RGB : Tape Reel ; Pb – Free; Halogen – Free

ABSOLUTE MAXIMUM RATINGS

($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	V_{DS}	-30	V	
Gate –Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current($T_J=150^{\circ}\text{C}$)	I_D	$T_A=25^{\circ}\text{C}$	-3.6	A
		$T_A=70^{\circ}\text{C}$	-3.0	
Pulsed Drain Current	I_{DM}	-15	A	
Continuous Source Current(Diode Conduction)	I_S	-1.0	A	
Power Dissipation	P_D	$T_A=25^{\circ}\text{C}$	1.25	W
		$T_A=70^{\circ}\text{C}$	0.8	
Operating Junction Temperature	T_J	150	$^{\circ}\text{C}$	
Storage Temperature Range	T_{STG}	-55/150	$^{\circ}\text{C}$	
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	375	$^{\circ}\text{C}/\text{W}$	



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ELECTRICAL CHARACTERISTICS

(TA=25°C Unless otherwise noted)

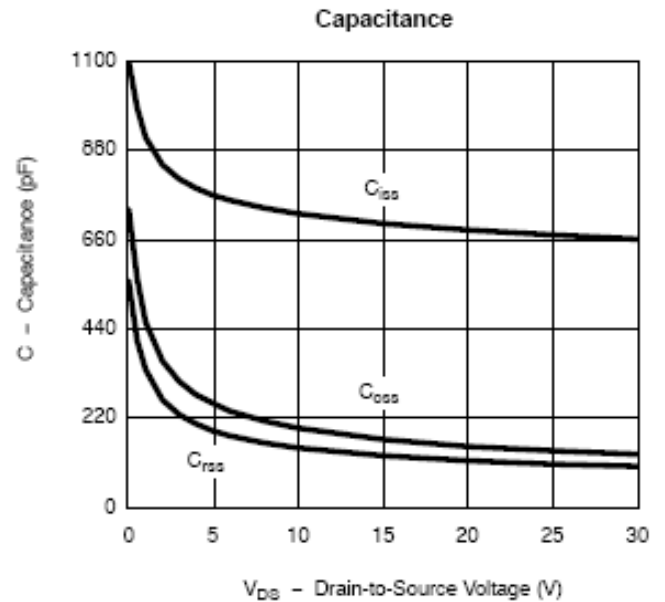
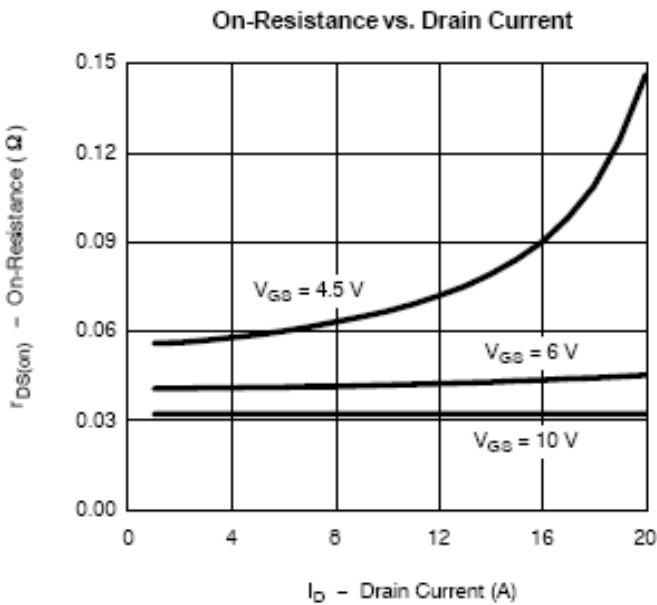
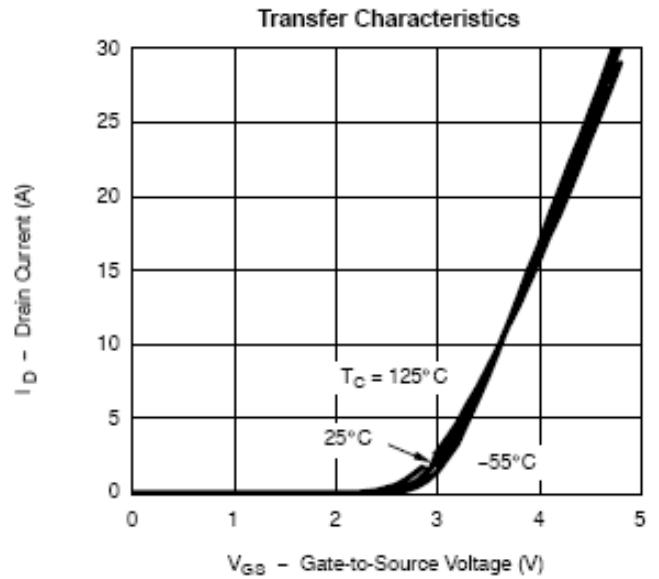
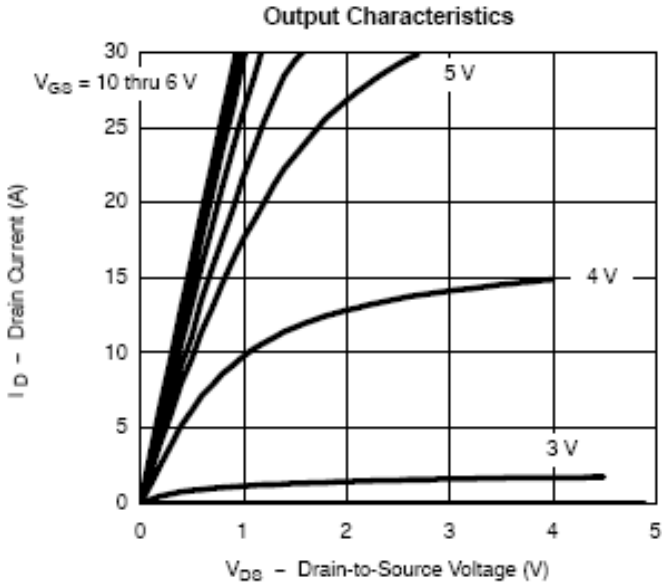
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250uA	-30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-0.8		-2.5	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V			-1	uA
		V _{DS} =-24V, V _{GS} =0V T _J =55°C			-10	
On-State Drain Current	I _{D(on)}	V _{DS} ≤ -5V, V _{GS} =-10V	-10			A
Drain-Source On-Resistance	R _{DSS(on)}	V _{GS} =-10V, I _D =-4.0A		0.062	0.070	Ω
		V _{GS} =-4.5V, I _D =-3.2A		0.085	0.095	
Forward Transconductance	g _{fs}	V _{DS} =-5.0V, I _D =-4.0A		10		S
Diode Forward Voltage	V _{SD}	I _S =-1.0A, V _{GS} =0V		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =-15V, V _{GS} =-10V I _D =-3.5A		10	18	nC
Gate-Source Charge	Q _{gs}			1.6		
Gate-Drain Charge	Q _{gd}			3.0		
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V f=1MHz		450		pF
Output Capacitance	C _{oss}			95		
Reverse Transfer Capacitance	C _{rss}			55		
Turn-On Time	t _{d(on)}	V _{DD} =-15V, R _L =15Ω I _D =-1.0A, V _{GEN} =-10V R _G =6Ω		8	18	nS
	t _r			8	18	
Turn-Off Time	t _{d(off)}			25	50	
	t _f			25	35	



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TYPICAL CHARACTERISTICS

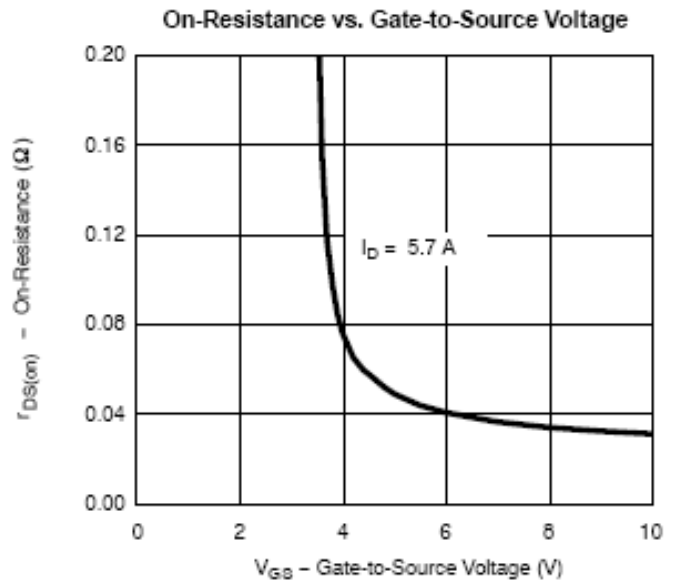
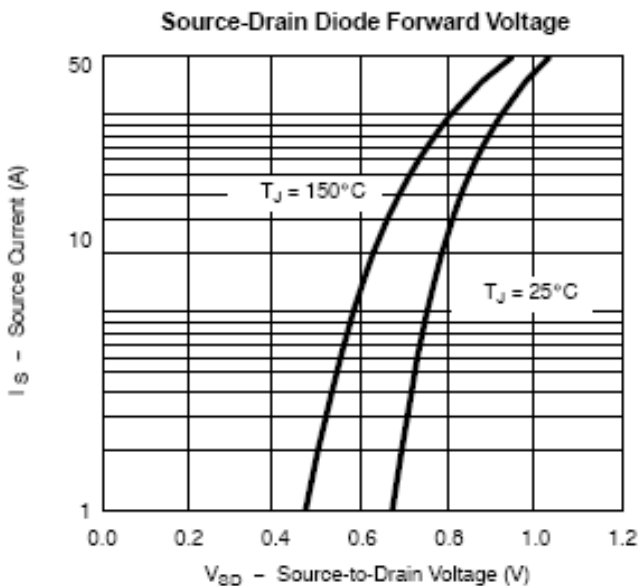
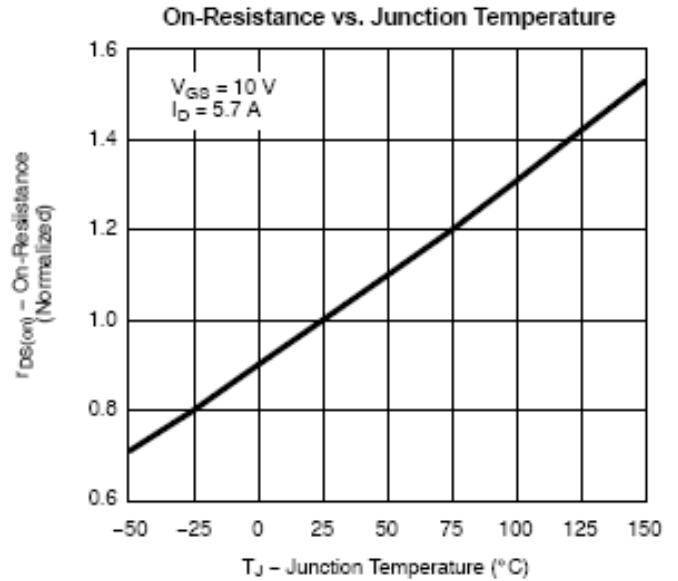
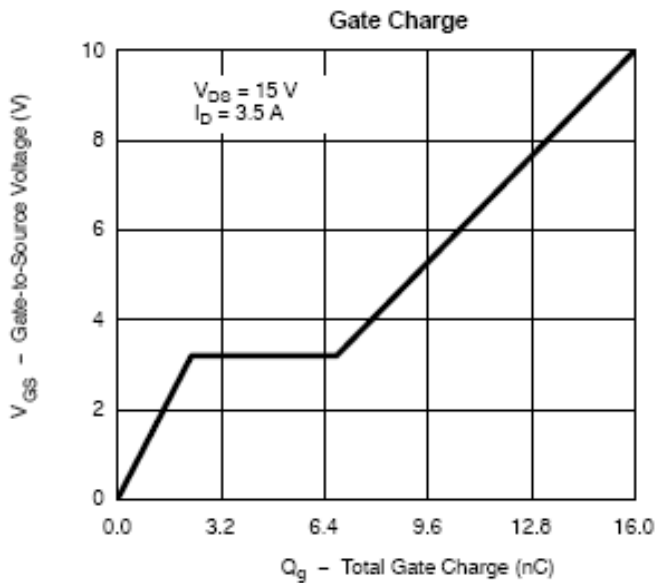




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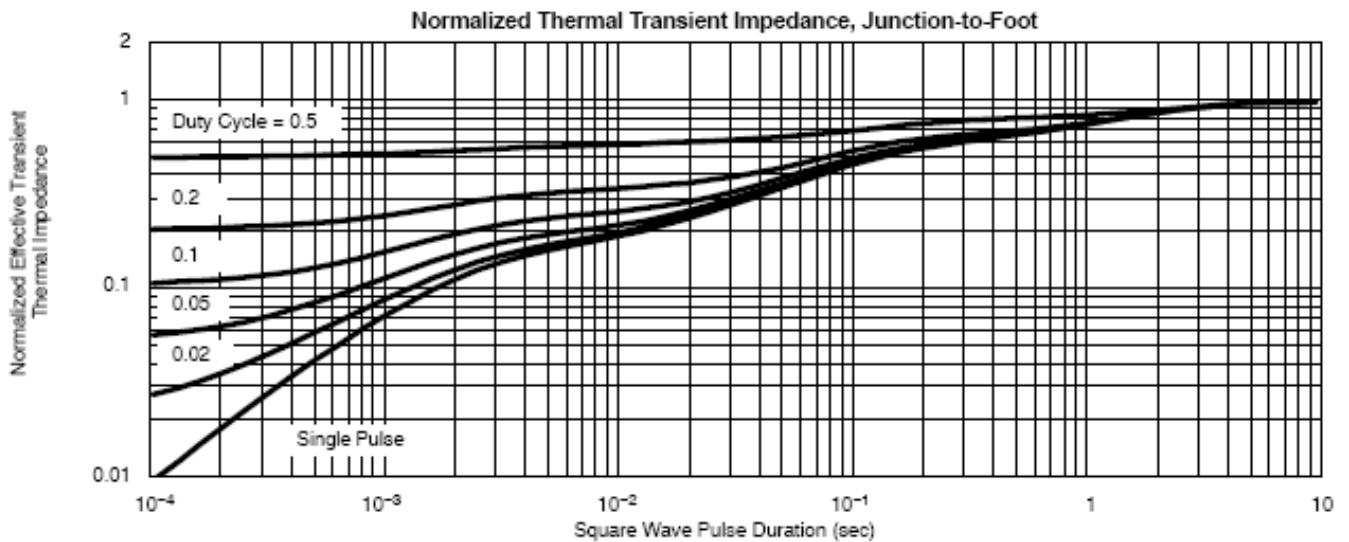
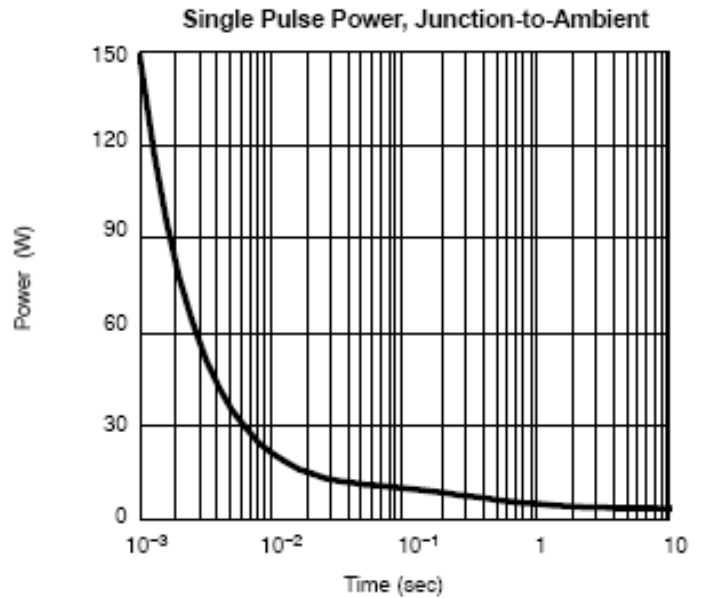
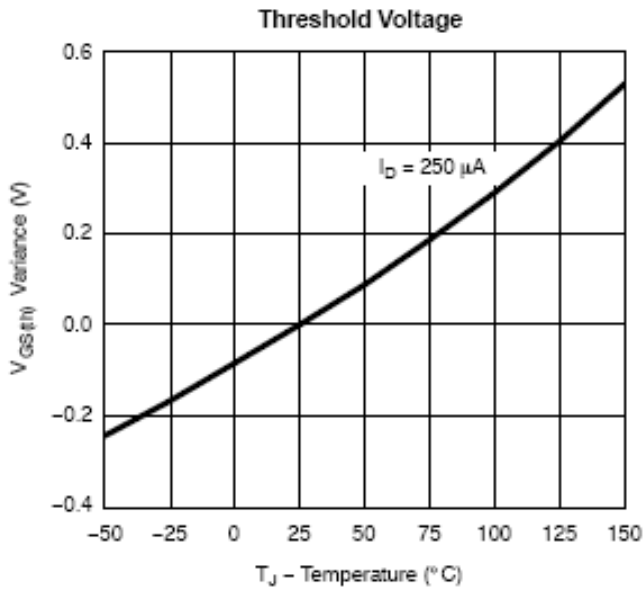




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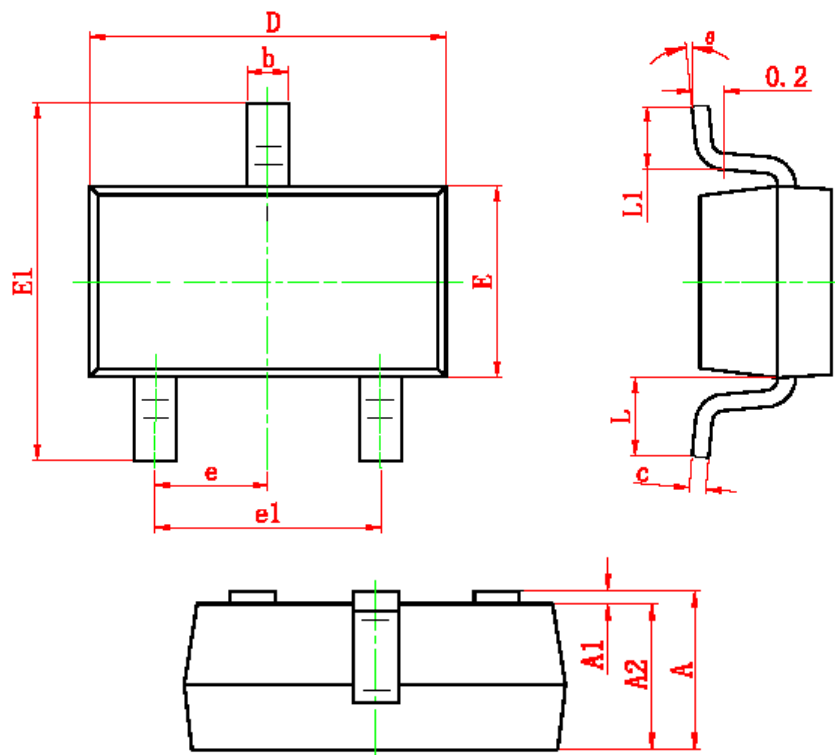




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SOT-23 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°



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